

Orion III Plasma Enhanced Chemical Vapor Deposition (PECVD)



Plasma initiated by applying a strong radio frequency electromagnetic field to the wafer platter is used to deposit oxides and nitrides. Specification

- ICP source of 600 W and 13.56 MHz RF Generator
- Helium backside cooling
- Laser endpoint detection

Film deposited

- Oxides
- Oxynitrides
- Nitrides
- Amorphous Silicon